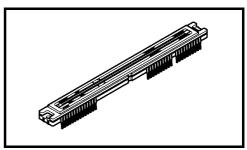
TOSHIBA CCD Linear Image Sensor CCD (Charge Coupled Device)

# TENTATIVE

# **TCD2713DG**

The TCD2713DG is a high sensitive and low dark current 7500 pixels  $\times$  4 line CCD color image sensor. The sensor is designed for color scanner.

The device contains a row of 7500 pixels  $\times$  4 line photodiodes which provide a 24 lines/mm across a A3 size paper.



Weight: 16.0 g (typ.)

#### **Features**

Number of image sensing pixels : 30000 pixels (7500 pixels × 4 line)
Image sensing pixels size : 9.325 µm by 9.325 µm on 9.325 µm center

Photo sensing region : High sensitive pn photodiode

• Clock : 2-phase (5 V)

• Distance between photodiode array

:Pixel B to pixel G: 18.65 μm (2 lines) Pixel G to pixel R: 18.65 μm (2 lines) Pixel R to pixel B/W: 55.95 μm (6 lines)

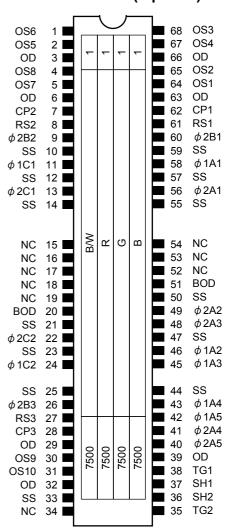
Internal circuit: Clamp circuit
Package : 68-pin CERDIP
Color filter : Red, Green, Blue

### **Maximum Ratings (Note 1)**

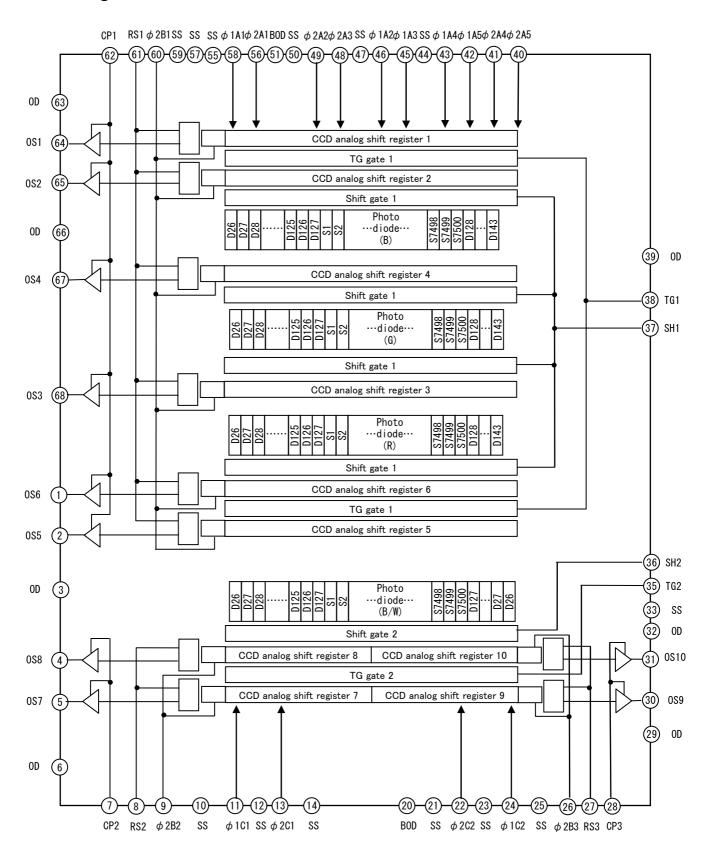
Characteristics	Symbol	Rating	Unit
Clock pulse voltage	$V_{\phi A}$		
Clock pulse voltage	$V_{\phi C}$		
Last stage clock pulse voltage	$V_{\phi B}$		
Shift pulse voltage	V <sub>SH</sub>	-0.3~8	V
Reset pulse voltage	V <sub>RS</sub>		
Clamp pulse voltage	V <sub>CP</sub>	1	
TG pulse voltage	V <sub>TG</sub>		
Power supply voltage	V <sub>OD</sub>	-0.3~13.5	V
Bias power supply voltage	V <sub>BOD</sub>	-0.5~15.5	
Operating temperature	t <sub>opr</sub>	0~60	°C
Storage temperature	t <sub>stg</sub>	-25~85	°C

Note 1: All voltages are with respect to SS pins (ground)

### **PIN Connections (top view)**



### **Circuit Diagram**



### **Pin Names**

Pin No.	Symbol	Name	Pin No.	Symbol	Name
1	OS6	Output signal 6 (RED(EVEN))	35	TG2	TG Gate 2
2	OS5	Output signal 5 (RED(ODD))	36	SH2	Shift gate 2
3	OD	Power supply(RED)	37	SH1	Shift gate 1
4	OS8	Output signal 8 (B/W-F(EVEN))	38	TG1	TG Gate 1
5	OS7	Output signal 7 (B/W-F(ODD))	39	OD	Power supply(COLOR)
6	OD	Power supply(B/W-F)	40	φ2 <b>A</b> 5	Transfer clock (phase 2) COLOR
7	CP2	Clamp gate 2 B/W	41	ф2А4	Transfer clock (phase 2) COLOR
8	RS2	Reset gate 2 B/W	42	ф1А5	Transfer clock (phase 1) COLOR
9	φ2B2	Last stage clock (phase 2) B/W	43	ф1А4	Transfer clock (phase 1) COLOR
10	SS	Ground	44	SS	Ground
11	φ1C1	Transfer clock (phase 1)B/W	45	φ1A3	Transfer clock (phase 1) COLOR
12	SS	Ground	46	φ1A2	Transfer clock (phase 1) COLOR
13	φ2C1	Transfer clock (phase 2)B/W	47	SS	Ground
14	SS	Ground	48	φ2 <b>A3</b>	Transfer clock (phase 2) COLOR
15	NC	No connect	49	φ2 <b>A2</b>	Transfer clock (phase 2) COLOR
16	NC	No connect	50	SS	Ground
17	NC	No connect	51	BOD	Bias power supply
18	NC	No connect	52	NC	No connect
19	NC	No connect	53	NC	No connect
20	BOD	Bias power supply	54	NC	No connect
21	SS	Ground	55	SS	Ground
22	φ2C2	Transfer clock (phase 2) B/W	56	φ2A1	Transfer clock (phase 2) COLOR
23	SS	Ground	57	SS	Ground
24	φ1C2	Transfer clock (phase 1) B/W	58	φ1Α1	Transfer clock (phase 1) COLOR
25	SS	Ground	59	SS	Ground
26	ф2В3	Last stage clock (phase 2) B/W	60	φ2B1	Last stage clock (phase 2) COLOR
27	RS3	Reset gate 3 B/W	61	RS1	Reset gate 1 COLOR
28	CP3	Clamp gate 3 B/W	62	CP1	Clamp gate 1 COLOR
29	OD	Power supply(B/W-L)	63	OD	Power supply (BLUE)
30	OS9	Output signal 9 (B/W-L(ODD))	64	OS1	Output signal 1 (BLUE(ODD))
31	OS10	Output signal 10 (B/W-L(EVEN))	65	OS2	Output signal 2 (BLUE(EVEN))
32	OD	Power supply(B/W)	66	OD	Power supply(GREEN)
33	SS	Ground	67	OS4	Output signal 4 (GREEN(EVEN))
34	NC	No connect	68	OS3	Output signal 3 (GREEN(ODD))

### **Optical/Electrical Characteristics**

(Ta = 25°C,  $V_{OD} = V_{BOD} = 10$  V,  $V_{\phi} = V_{SH} = V_{RS} = V_{CP} = V_{TG} = 5$  V (pulse),  $f_{\phi} = 1$  MHz, load resistance = 100 k $\Omega$ ,  $t_{INT}$  (integration time) = 10 ms, light source = A light source + CM500S filter (t = 1.0 mm))

#### ●COLOR Part

Characteristics		Symbol	Min	Тур.	Max	Unit	Note
	Red	R (R)	9.2	13.1	17.0		
Sensitivity	Green	R (G)	12.9	18.4	23.9	V/lx·s	(Note 2)
	Blue	R (B)	5.3	7.6	9.8		
Photo response non uniformity		PRNU (1)	_	10	20	%	(Note 3)
		PRNU (3)	_	3	12	mV	(Note 4)
Saturation output voltage		V <sub>SAT</sub>	1.8	2.0	_	V	(Note 5)
Saturation exposure		SE	0.07	_	_	lx·s	(Note 6)
Dark signal voltage		V <sub>DRK</sub>	_	3	6	mV	(Note 7)
Dark signal non uniform	ity	DSNU	_	8	12	mV	(Note 8)
Dc power dissipation		P <sub>D</sub>	_	550	770	mW	_
Total transfer efficiency		TTE	92	98		%	_
Output impedance		ZO	_	0.2	0.5	kΩ	_
Dc signal output voltage		Vos	4.0	5.0	6.0	V	(Note 9)
Random noise		$N_{D\sigma}$	_	1.0	_	mV	(Note 10)

### ●B/W Part

Characteristics	Symbol	Min	Тур.	Max	Unit	Note
Sensitivity	R (B/W)	19.0	23.8	28.5	V/lx·s	(Note 2)
Photo response non uniformity	PRNU (1)	_	10	20	%	(Note 3)
Frioto response non uniformity	PRNU (3)	_	3	12	mV	(Note 4)
Saturation output voltage	Vsat	1.8	2.0	_	V	(Note 5)
Saturation exposure	SE	0.06	_	_	lx·s	(Note 6)
Dark signal voltage	V <sub>DRK</sub>	_	3	6	mV	(Note 7)
Dark signal non uniformity	DSNU	_	8	12	mV	(Note 8)
Dc power dissipation	P <sub>D</sub>	_	450	660	mW	_
Total transfer efficiency	TTE	92	98	_	%	_
Output impedance	ZO	_	0.2	0.5	kΩ	_
Dc signal output voltage	Vos	3.3	4.3	5.3	V	(Note 9)
Random noise	N <sub>Dσ</sub>		0.7	_	mV	(Note 10)

- Note 2:Sensitivity is defined for each color of signal outputs average when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.
- Note 3:PRNU (1) is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.

PRNU (1) = 
$$\frac{\Delta \chi}{\overline{\chi}} \times 100$$
 (%)

 $\bar{\chi}$  : Average of total signal outputs

 $\Delta \chi$ : The maximum deviation from  $\bar{\chi}$ .

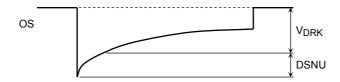
Note 4:PRNU (3) is defined as maximum voltage with next pixel, where measured 5% of SE (typ.).

Note 5:V<sub>SAT</sub> is defined as minimum saturation output voltage of all effective pixels.

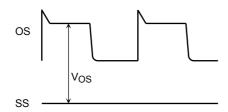
Note 6:Definition of SE: 
$$SE = \frac{V_{SAT}}{RG}$$

Note 7:V<sub>DRK</sub> is defined as average dark signal voltage of all effective pixels.

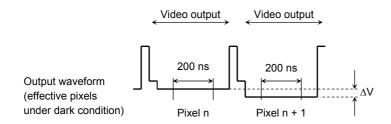
Note 8:DSNU is defined by the difference between average value (V<sub>DRK</sub>) and the maximum value of the dark voltage.



Note 9:DC signal output voltage is defined as follows:



Note 10:Random noise is defined as the standard deviation (sigma) of the output level difference between two adjacent effective pixels under no illumination (i.e. dark condition) calculated by the following procedure.



- 1) Two adjacent pixels (pixel n and n + 1) in one reading are fixed as measurement points.
- 2) Each of the output levels at video output periods averaged over 200 nanosecond period to get Vn and Vn + 1.
- 3) Vn + 1 is subtracted from Vn to get  $\Delta V$ .

$$\Delta V = Vn - Vn + 1$$

4) The standard deviation of  $\Delta V$  is calculated after procedure 2) and 3) are repeated 30 times (30 readings).

$$\Delta V = \frac{1}{30} \sum_{i=1}^{30} \Delta Vi$$

$$\sigma = \sqrt{\frac{1}{30} \sum_{i=1}^{30} \left| \Delta Vi \right| - \overline{\Delta V} \right|^2}$$

5) Procedure 2), 3) and 4) are repeated 10 times to get 10 sigma values.

$$\overline{\sigma} = \frac{1}{10} \sum_{j=1}^{10} \sigma_j$$

6)  $\overline{\sigma}$  value calculated using the above procedure is observed  $\sqrt{2}$  times larger than that measured relative to the ground level. So we specify the random noise as follows.

Random noise = 
$$\frac{1}{\sqrt{2}} \overline{\sigma}$$

# Operating Condition (Ta = 25°C)

Characteristic	cs	Symbol	Min	Тур.	Max	Unit
Clock pulse voltage	"H" level	$V_{\phi 1A}, V_{\phi 2A}$	4.75	5	5.5	V
Clock pulse voltage	"L" level	$V_{\varphi 1C,}V_{\varphi 2C}$	0	_	0.25	V
Final stage clock pulse	"H" level	V/	4.75	5	5.5	V
voltage	"L" level	$V_{\phi 2B}$	0	_	0.25	V
Shift pulse voltage	"H" level	V	4.75	5	5.5	V
, ,	"L" level	V <sub>SH</sub>	0	_	0.25	V
	"H" level	V <sub>RS</sub>	4.75	5	5.5	V
Reset pulse voltage	"L" level		0	_	0.25	] v
Claren mulas valtaria	"H" level	V <sub>CP</sub>	4.75	5	5.5	V
Clamp pulse voltage	"L" level		0	_	0.25	V
TO	"H" level		4.75	5	5.5	.,
TG pulse voltage	"L" level	$V_{TG}$	0	_	0.25	V
Power supply voltage		V <sub>OD</sub>	9.5	10	10.5	
Bias power supply voltag	e (Note 11)	V <sub>BOD</sub>	9.5	10	10.5	V

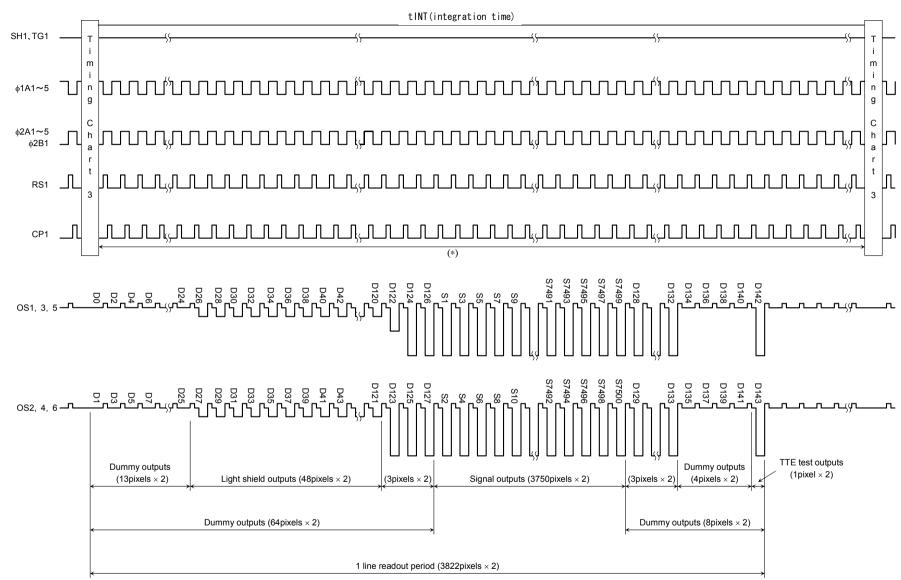
Note 11: Please impress the voltage to  $V_{\mbox{\footnotesize{BOD}}}$  regardless of driving line.

# Clock Characteristics (Ta = 25°C)

Characteristics	Symbol	Min	Тур.	Max	Unit
Clock pulse frequency	$f_{\varphi}$	_	1	35	MHz
Reset pulse frequency	f <sub>RS</sub>	_	1	35	MHz
Clamp pulse frequency	f <sub>CP</sub>	_	1	35	MHz
Clock capacitance (Note 12)	С <sub>ф</sub> А	_	160	_	pF
Clock capacitance (Note 12)	$C_{\phiC}$	_	170	_	pF
Final stage clock capacitance	СфВ	_	10	_	pF
Shift gate capacitance	C <sub>SH</sub>	_	30	_	pF
Reset gate capacitance	C <sub>RS</sub>	_	10	_	pF
Clamp gate capacitance	C <sub>CP</sub>	_	10	_	pF
TG gate capacitance	C <sub>TG</sub>	_	10	_	pF

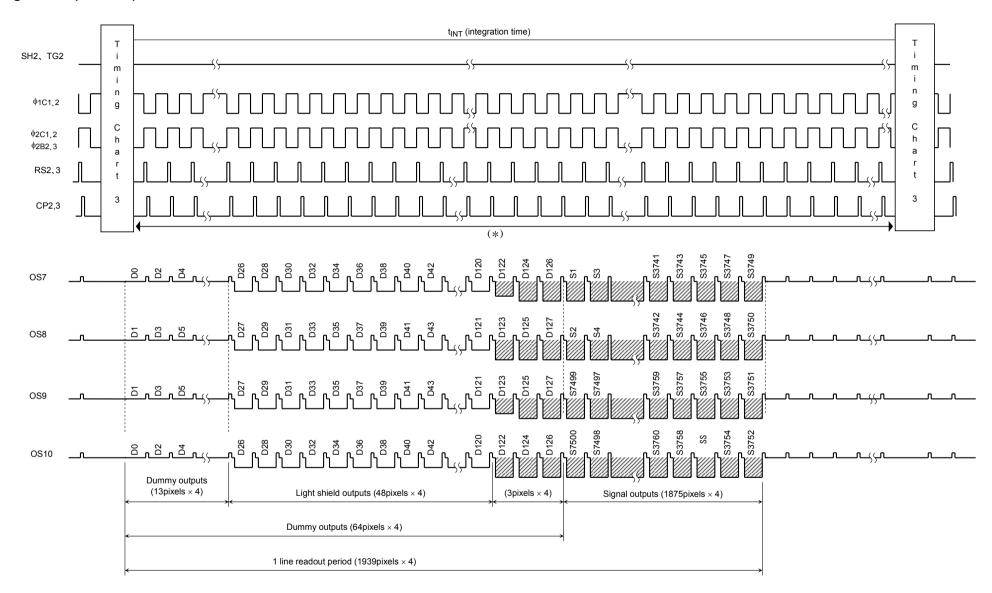
Note 12: $V_{OD} = V_{BOD} = 10 \text{ V}$ 

### Timing Chart 1: (color part)



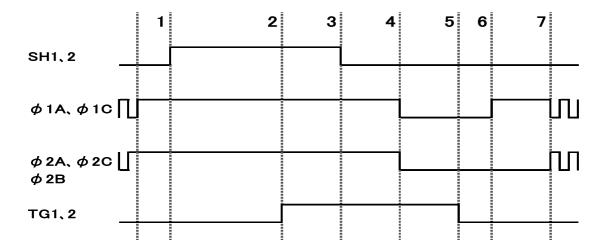
<sup>\*:</sup> Hold the TG1 and SH1 pins at low during this period.

### Timing Chart 2 (B/W Part)

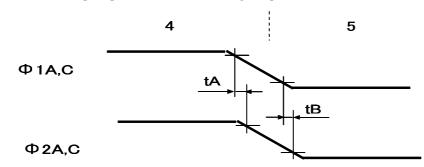


<sup>\*:</sup>Hold the TG2 and SH2 pins at low during this period.

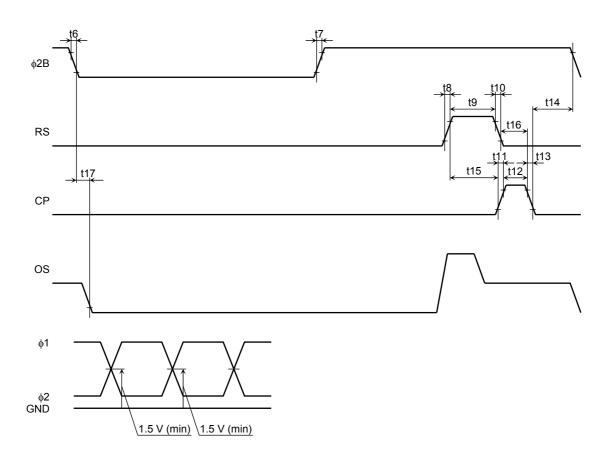
### **Timing Chart 3**



Note13: Each RS and CP pins put to LOW level during the period of the above mentioned address 1-7.



### **Timing Requirements 1**



Characteristics		Symbol	Min	Typ. (Note 14)	Max	Unit
φ1, φ2 Pulse rise time, fall time		t6, t7	0	50	_	ns
RS pulse rise time, fall time		t8, t10	0	20	_	ns
RS pulse width		t9	6	100	_	ns
CP pulse rise time, fall time		t11, t13	0	20	_	ns
CP pulse width		t12	6	200	_	ns
Pulse timing of \$\phi 2B\$ and CP		t14	0	40	_	ns
Pulse timing of RS and CP		t15	0	0	_	ns
Fuise uning of NS and CF		t16	6	100	_	ns
Video data delay time (	(Note 15)	t17		7	_	ns

Note14:Measured with fRS=1MHz

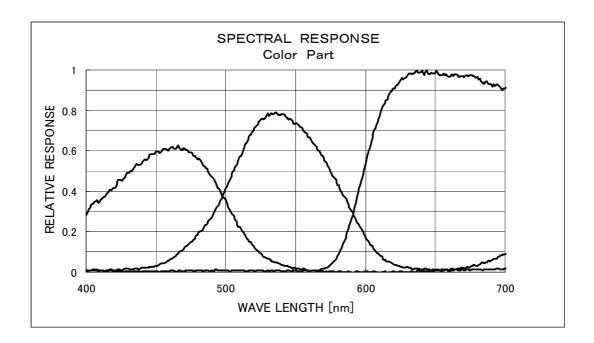
Note15:Load resistance is  $100k\Omega$ 

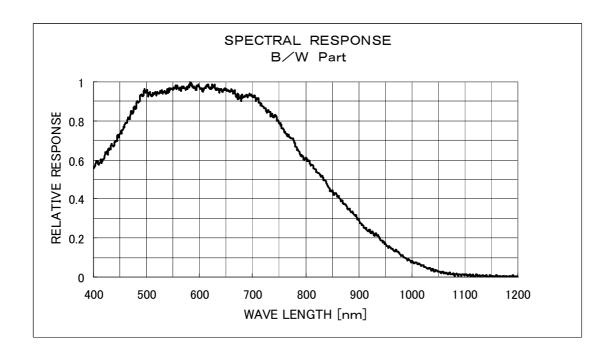
# **Timing Requirements 2**

Timing Address	Min	Тур	Max	Unit
1	250	500	_	ns
2	1000	2000	_	ns
3	500	1000	_	ns
4	500	1000	_	ns
5	500	1000	_	ns
6	250	500	_	ns
7	500	1000	_	ns
Vertical Transfer Time	3.5	7	_	μs

	記号	最小	標準	最大	単位
$\phi$ 1A- $\phi$ 2A( $\phi$ 1C- $\phi$ 2C) Pulse timing	tA	-0.5	0	0.5	ns
	tB	-0.5	0	0.5	ns

### **Spectral Response**





#### Caution

#### 1. Electrostatic Breakdown

The dust and stain on the glass window of the package degrade optical performance of CCD sensor. Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

Prevent the generation of static electricity due to friction by making the work with bare hands or by putting on cotton gloves and non-charging working clothes.

Discharge the static electricity by providing earth plate or earth wire on the floor, door or stand of the work room

Ground the tools such as soldering iron, radio cutting pliers of or pincer.

It is not necessarily required to execute all precaution items for static electricity.

It is all right to mitigate the precautions by confirming that the trouble rate within the prescribed range.

#### 2. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor. Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2. Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

### 3. Incident Light

CCD sensor is sensitive to infrared light. Note that infrared light component degrades resolution and PRNU of CCD sensor.

### 4. Mounting on a PCB

This package is sensitive to mechanical stress.

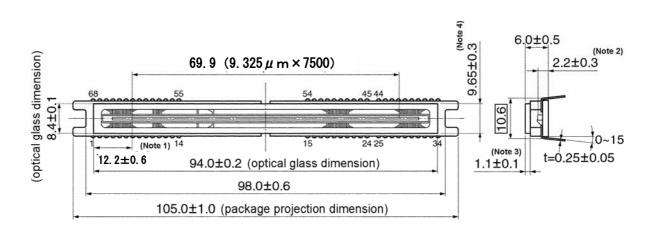
Toshiba recommends using IC inserters for mounting, instead of using lead forming equipment.

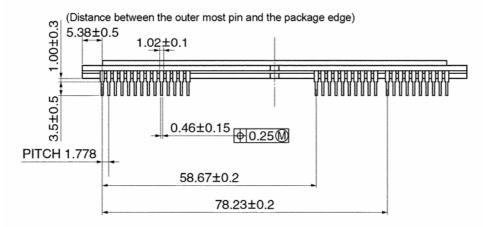
#### 5. Soldering

Soldering by the solder flow method cannot be guaranteed because this method may have deleterious effects on prevention of window glass soiling and heat resistance.

Using a soldering iron, complete soldering within three seconds for lead temperatures of up to 380°C.

### **Package Dimensions**





- Note 1: Distance between the center of the first pin and the first pixel (S1)
- Note 2: Distance between the of the chip and bottom of the package.
- Note 3: Glass thickness (n = 1.5)
- Note 4: Dimensional tolerance is ±0.3 mm for the 10-mm range from each ceramic edge, ±0.4 mm for the 10-mm to 27-mm range and ±0.5 mm for the inner range.

Weight: 16.0 g (typ.)

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